

Cheng-Hsun-Tony Chang

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

109
citations

1307594

7
h-index

1372567

10
g-index

20
all docs

20
docs citations

20
times ranked

144
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced exchange bias fields for CoO/Co bilayers: influence of antiferromagnetic grains and mechanisms. <i>Applied Surface Science</i> , 2017, 405, 316-320.	6.1	14
2	Tuning coercive force by adjusting electric potential in solution processed Co/Pt(111) and the mechanism involved. <i>Scientific Reports</i> , 2017, 7, 43700.	3.3	10
3	Enhancing the magnetic anisotropy energy by tuning the contact areas of Ag and Ni at the Ag/Ni interface. <i>Physical Chemistry Chemical Physics</i> , 2018, 20, 1504-1512.	2.8	10
4	Enhancement of the polar coercive force for annealed Co/Ir(111) ultrathin films. <i>Journal of the Korean Physical Society</i> , 2013, 62, 1945-1949.	0.7	9
5	Pinning of magnetic moments at the interfacial region of ultrathin CoO/Co bilayers grown on Ge(100). <i>Applied Surface Science</i> , 2015, 354, 95-99.	6.1	9
6	Enhancing silicide formation in Ni/Si(111) by Ag-Si particles at the interface. <i>Scientific Reports</i> , 2019, 9, 8835.	3.3	8
7	A practical method for fabricating superparamagnetic films and the mechanism involved. <i>Nanoscale</i> , 2020, 12, 14096-14105.	5.6	8
8	Interaction transfer of silicon atoms forming Co silicide for Co/ 3Å–3R30Å°-Ag/Si(111) and related magnetic properties. <i>Journal of Applied Physics</i> , 2015, 117, 17B733.	2.5	7
9	Variation of blocking temperatures for exchange biased CoO/Co/Ge(100) films. <i>AIP Advances</i> , 2016, 6, .	1.3	7
10	Hot Carrier Stress Sensing Bulk Current for 28 nm Stacked High-k nMOSFETs. <i>Electronics (Switzerland)</i> , 2020, 9, 2095.	3.1	6
11	Electric field modifications on the coercive force for electrochemical etched Co/Pt(111) films. <i>Surface and Coatings Technology</i> , 2016, 303, 136-140.	4.8	4
12	The straightforward fabrication of thin silicide layers at low temperatures by employing the molecular-incident reaction effect. <i>Results in Physics</i> , 2022, 39, 105778.	4.1	4
13	Structural determination and magnetic properties for Coâ€“rubrene composite films on Si(100). <i>Applied Surface Science</i> , 2015, 354, 139-143.	6.1	3
14	Comparisons of magnetic defects and coercive forces for Co/Si(100) and Co/rubrene/Si(100). <i>Physical Chemistry Chemical Physics</i> , 2020, 22, 14900-14909.	2.8	3
15	Compositions and Magnetic Properties of CoO/Co/Ge(111) Films. <i>IEEE Transactions on Magnetics</i> , 2014, 50, 1-4.	2.1	2
16	Uniformity of Gate Dielectric for I/O and Core HK/MG pMOSFETs with Nitridation Treatments. <i>Journal of Electronic Materials</i> , 2020, 49, 6764-6775.	2.2	2
17	Self-assembled magnetic heterostructure of Co/DLC films. <i>Nanotechnology</i> , 2021, 32, 495709.	2.6	2
18	Silica Layer Used in Sensor Fabrication from a Low-Temperature Silane-Free Procedure. <i>Chemosensors</i> , 2021, 9, 32.	3.6	1

#	ARTICLE	IF	CITATIONS
19	Integrity of n-type channel surface for nano-node high-k gate dielectric. , 2021, , .		0
20	ON/OFF current of nano-node field-effect transistors on p-substrate or SOI substrate. , 2021, , .		0